

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
12 February 2004 (12.02.2004)

PCT

(10) International Publication Number
WO 2004/013890 A2

(51) International Patent Classification⁷:

H01J 49/00

(21) International Application Number:

PCT/EP2003/008354

(22) International Filing Date: 29 July 2003 (29.07.2003)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
0217815.0 1 August 2002 (01.08.2002) GB

(71) Applicant (for all designated States except US): MICRO-
SAIC SYSTEMS LIMITED [GB/GB]; 8 Clifford Street,
London W1S 2LQ (GB).

(72) Inventor; and

(75) Inventor/Applicant (for US only): SYMS, Richard
[GB/GB]; 59 Woodstock Avenue, Ealing, London W13
9UQ (GB).

(74) Agents: MOORE, Barry et al.; Hanna Moore & Curley,
11 Mespil Road, Dublin 4 (IE).

(81) Designated States (national): AE, AG, AL, AM, AT, AU,
AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU,
CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GB, GH,
GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC,
LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW,
MX, MZ, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC,
SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA,
UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

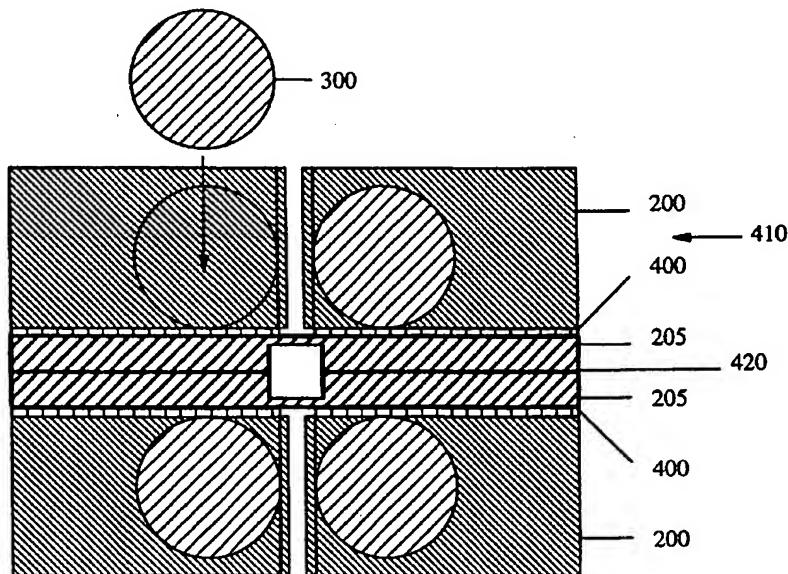
(84) Designated States (regional): ARIPO patent (GH, GM,
KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW),
Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM),
European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE,
ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO,
SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM,
GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— without international search report and to be republished
upon receipt of that report

For two-letter codes and other abbreviations, refer to the "Guid-
ance Notes on Codes and Abbreviations" appearing at the begin-
ning of each regular issue of the PCT Gazette.

(54) Title: MONOLITHIC MICRO-ENGINEERED MASS SPECTROMETER



(57) Abstract: A method of constructing a micro-engineered mass spectrometer from bonded silicon-on-insulator (BSOI) wafers is described with reference to a quadrupole spectrometer. The quadrupole geometry is achieved using two BSOI wafers (200), which are bonded together to form a monolithic block (410). Deep etched features and springs formed in the outer silicon layers are used to locate cylindrical metallic electrode rods (300). The precision of the assembly is determined by a combination of lithography and deep etching, and by the mechanical definition of the bonded silicon layers. Deep etched features formed in the inner silicon layers are used to define ion entrance and ion collection optics. Other features such as fluidic channels may be incorporated.

WO 2004/013890 A2